



# P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

• Case: SO-8

Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Terminal Connections: See Diagram Below

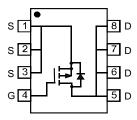
Marking Information: See Page 5

Ordering Information: See Page 5

Weight: 0.072 grams (approximate)







Top View Internal Schematic

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 3)	Steady State (V <sub>GS</sub> = -4.5)	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	I <sub>D</sub>	-7.3 -4.7	А
Pulsed Drain Current (Note 4)			I <sub>DM</sub>	-80	Α

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P <sub>D</sub>	1.3	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C	R <sub>0JA</sub>	96.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on 1 in. x 1 in. FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.
- 4. Repetitive rating, pulse width limited by junction temperature.

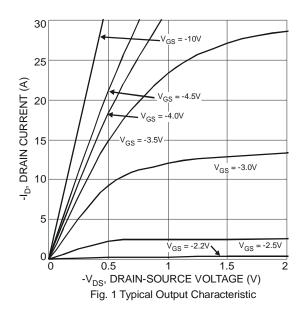


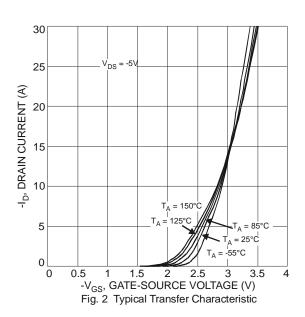
### Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	1	-	V	$V_{GS} = 0V$ , $I_D = -1mA$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	-1.7	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			13	16		$V_{GS} = -20V, I_{D} = -11A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	15	20	$\mathbf{m}\Omega$	$V_{GS} = -10V, I_D = -10A$	
	, ,		21	29		$V_{GS} = -5V, I_{D} = -5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	22	-	S	$V_{DS} = -5V, I_{D} = -10A$	
Diode Forward Voltage	V <sub>SD</sub>	-	-0.74	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C <sub>iss</sub>	-	1614	-	pF	15)( )( 0)(	
Output Capacitance	Coss	-	226	-	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	214	-	pF		
Gate Resistance	$R_{g}$	-	6.8	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge at 10V	Qq	-	35.4	-	nC	$V_{GS} = -10V, V_{DS} = -15V, I_{D} = -10A$	
Total Gate Charge at 5V	Qq	-	18.9	-	nC	V <sub>GS</sub> = -5V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -10A	
Gate-Source Charge	Q <sub>gs</sub>	-	4.6	-	nC		
Gate-Drain Charge	Q <sub>qd</sub>	-	5.7	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	8.6	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	12.7	-	ns	$V_{DS} = -15V, V_{GS} = -10V,$ $R_{L} = 1.5\Omega, R_{GEN} = 3\Omega,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	44.9	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	22.8	-	ns		

Notes:

- 5. Short duration pulse test used to minimize self-heating effect.
- 6. Guaranteed by design. Not subject to production testing.







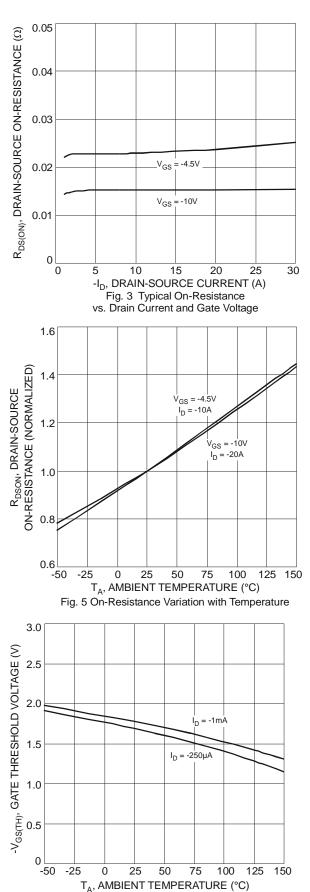


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

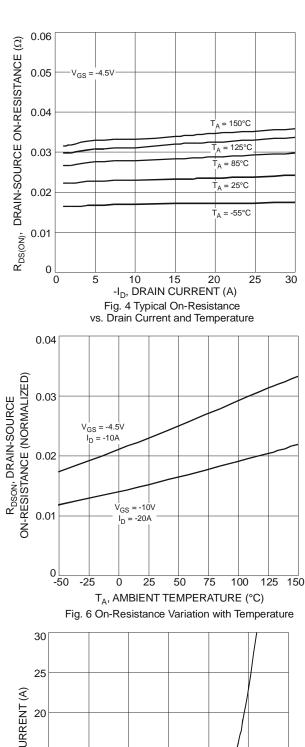
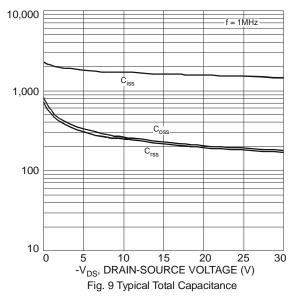
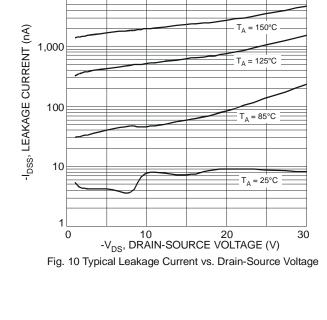


Fig. 8 Diode Forward Voltage vs. Current







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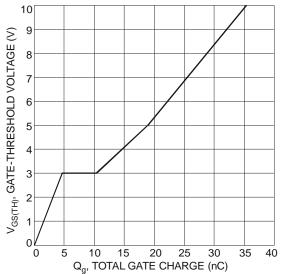


Fig. 11 Gate Threshold Voltage vs. Total Gate Charge

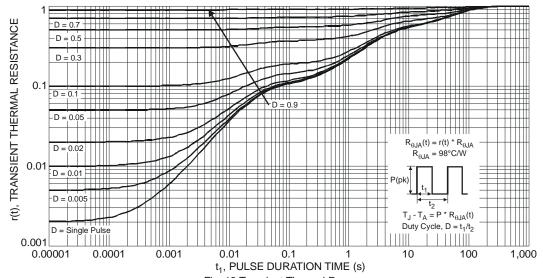


Fig. 12 Transient Thermal Response

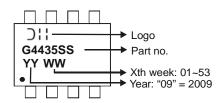


### Ordering Information (Note 7)

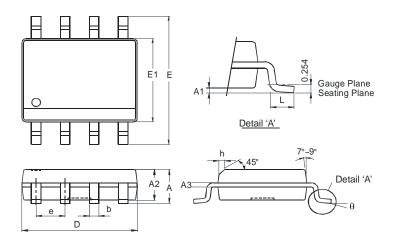
Part Number	Case	Packaging
DMG4435SSS-13	SO-8	2500 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

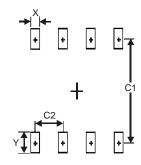


## **Package Outline Dimensions**



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
p	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	<b>e</b> 1.27 Typ			
h	ı	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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